

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☒ Surface-mounted package
- ☒ Advanced trench cell design

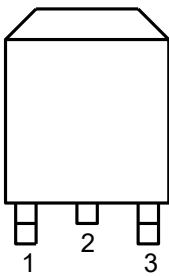
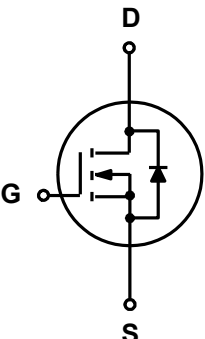
1.2 Applications

- ☒ LCD TV appliances
- ☒ LCDM appliances
- ☒ High power inverter system

1.3 Quick reference

- ☒ $BV \geq 40\text{ V}$
- ☒ $P_{tot} \leq 178\text{ W}$
- ☒ $I_D \leq 120\text{ A}$
- ☒ $R_{DS(ON)} \leq 0.95\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- ☒ $R_{DS(ON)} \leq 1.55\text{ m}\Omega @ V_{GS} = 6\text{ V}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate(G)	 Top View TO263-3L	
2	Drain(D)		
3	Source(S)		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C = 25\text{ }^{\circ}\text{C}$	-	40	V
V_{GS}	Gate-Source Voltage	$T_C = 25\text{ }^{\circ}\text{C}$	-	± 20	V
$I_{D^{*,***}}$	Drain Current (DC)	$T_C = 25\text{ }^{\circ}\text{C}, V_{GS} = 10\text{ V}$	-	120	A
		$T_C = 100\text{ }^{\circ}\text{C}, V_{GS} = 10\text{ V}$	-	120	A
$I_{DM^{*,**}}$	Drain Current (Pulsed)	$T_C = 25\text{ }^{\circ}\text{C}, V_{GS} = 10\text{ V}$	-	480	A
P_{tot}	Drain power dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	-	178	W
T_{stg}	Storage Temperature		- 55	150	$^{\circ}\text{C}$
T_J	Junction Temperature		-	150	$^{\circ}\text{C}$
I_S	Continuous-Source Current	$T_C = 25\text{ }^{\circ}\text{C}$	-	120	A
E_{AS}^*	Single Pulsed Avalanche Energy	$V_{DD} = 40\text{ V}, L = 1.0\text{ mH}$	-	2312	mJ
$R_{\theta JA}^*$	Thermal Resistance- Junction to Ambient		-	46	$^{\circ}\text{C/W}$
$R_{\theta JC}^*$	Thermal Resistance- Junction to Case		-	0.7	

Notes :

- * Surface Mounted on 1 in² pad area, $t \leq 10\text{ sec}$
- ** Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- *** Limited by bonding wire

4. Marking Information

Product Name	Marking
UP008N04DH	008N04H YWWXXX YWWXXX: Date Code

5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
UP008N04DH	TO263			800	

6. Electrical Characteristics ($T_A=25^\circ$ Unless Otherwise Noted)

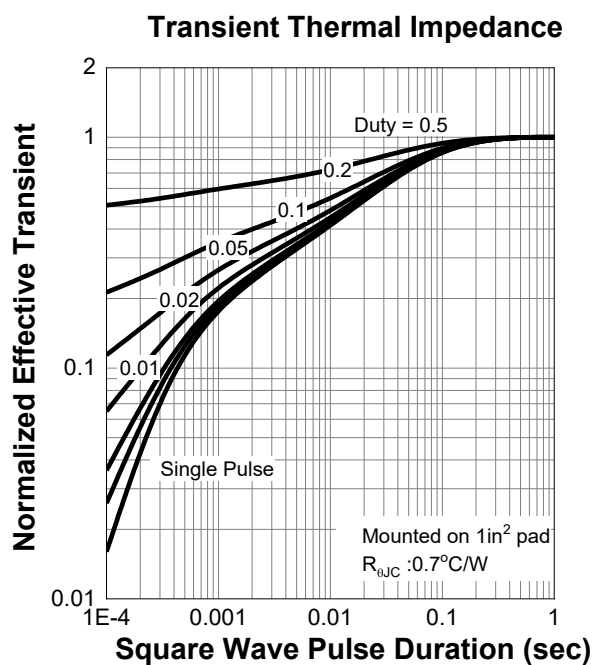
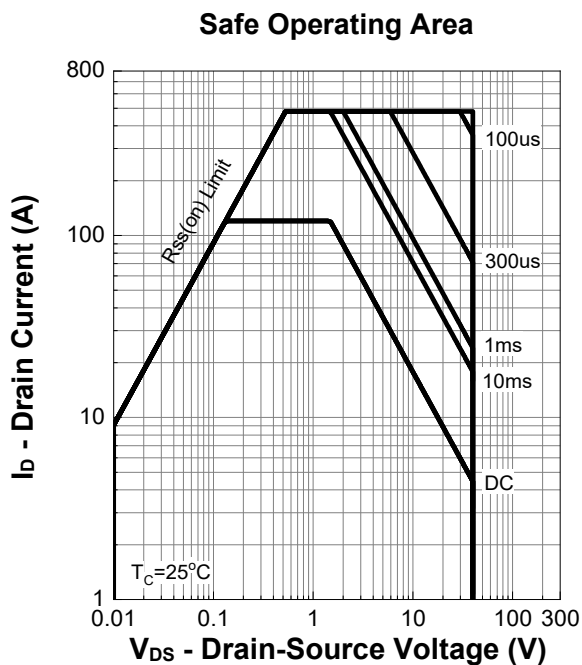
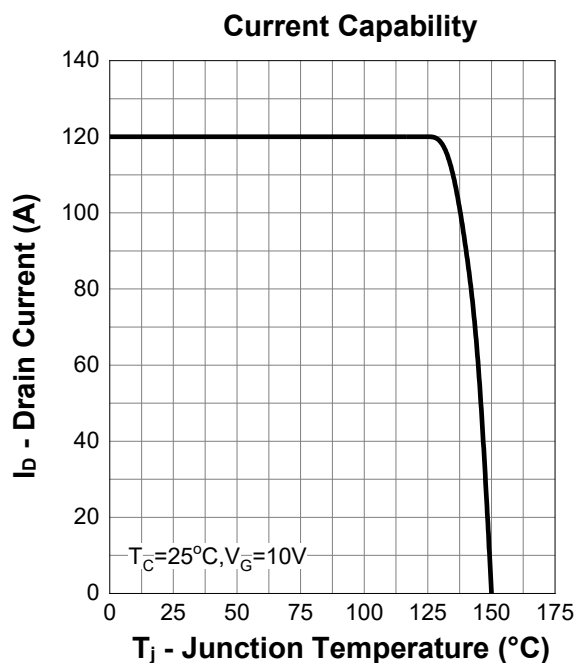
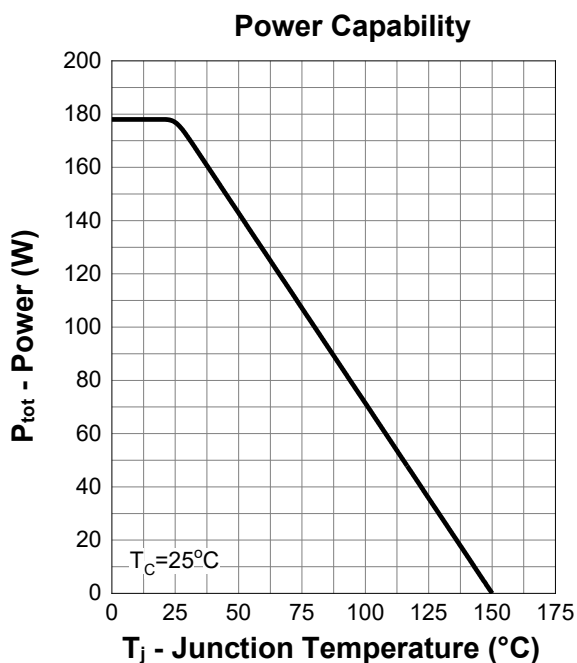
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _{DS} = 250 μA	40	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _{DS} = 250 μA	2	-	4	V
I _{DSS}	Drain Leakage Current	V _{DS} = 32 V, V _{GS} = 0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{GS} = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
R _{DS(ON)} ^a	On-State Resistance	V _{GS} = 10 V, I _{DS} = 30 A	-	0.85	0.95	m Ω
	On-State Resistance	V _{GS} = 6 V, I _{DS} = 20 A	-	1.25	1.55	m Ω
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} = 30 A, V _{GS} = 0 V	-	-	1.3	V
t _{rr}	Reverse Recovery Time	I _{DS} = 30 A, V _{GS} = 0 V dI _{SD} /dt = 100 A/μs	-	90	-	nS
Q _{rr}	Reverse Recovery Charge		-	130	-	nC
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} = 0 V, V _{DS} = 30 V Frequency = 1 MHz	-	8606	-	pF
C _{oss}	Output Capacitance		-	3780	-	
C _{rss}	Reverse Transfer Capacitance		-	87	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} = 20 V, V _{GEN} = 10 V, RG = 3.9 Ω, RL = 0.66 Ω, IDS = 30 A	-	30	-	nS
t _r	Turn-on Rise Time		-	125	-	
t _{d(off)}	Turn-off Delay Time		-	102	-	
t _f	Turn-off Fall Time		-	117	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} = 20 V, V _{GS} = 10 V, I _{DS} = 30 A	-	141	-	nC
Q _{gs}	Gate-Source Charge		-	44	-	
Q _{gd}	Gate-Drain Charge		-	31	-	

Notes :

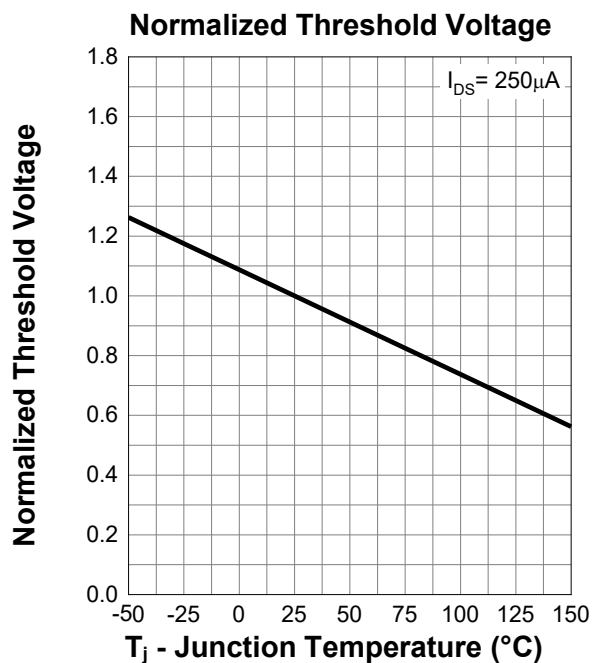
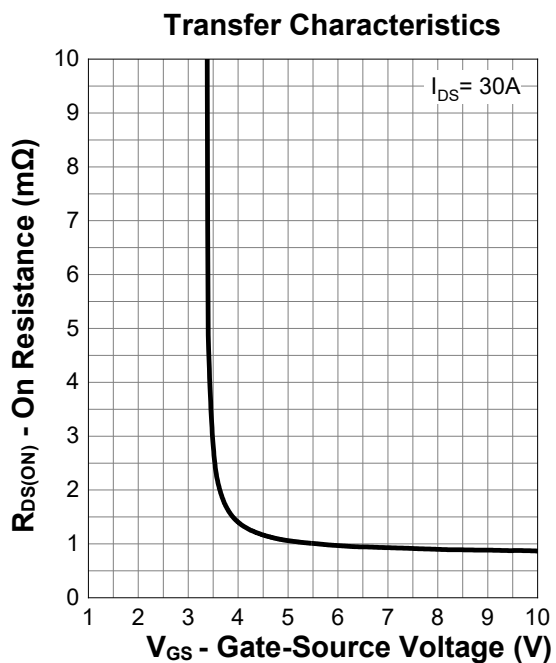
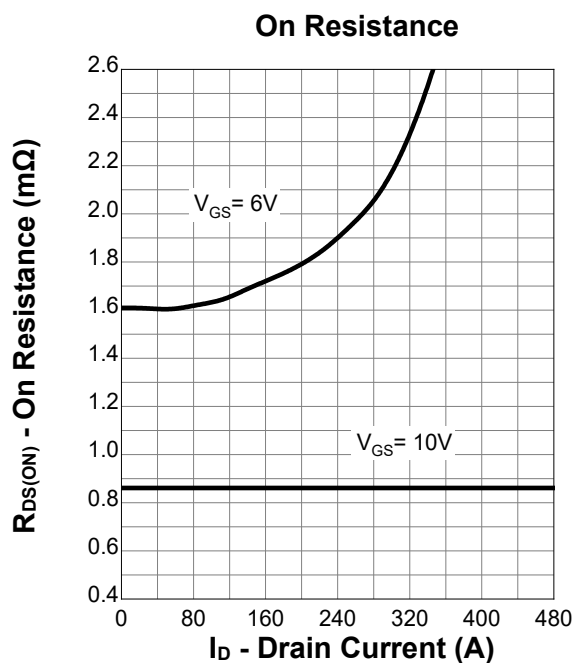
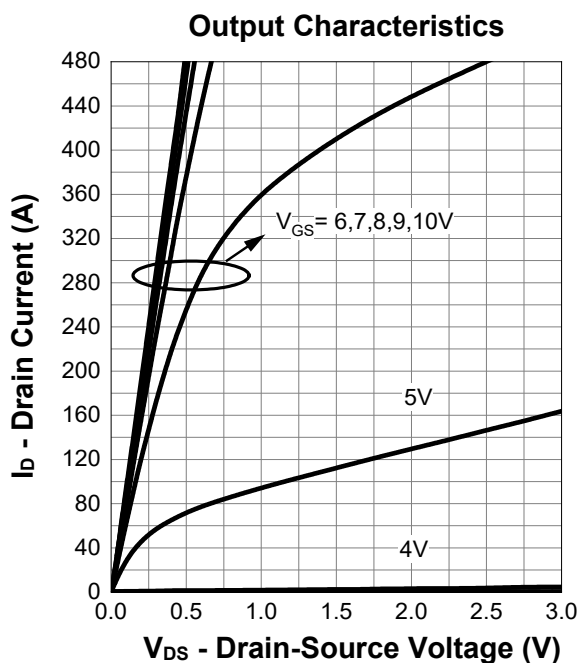
a : Pulse test ; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

b : Guaranteed by design, not subject to production testing

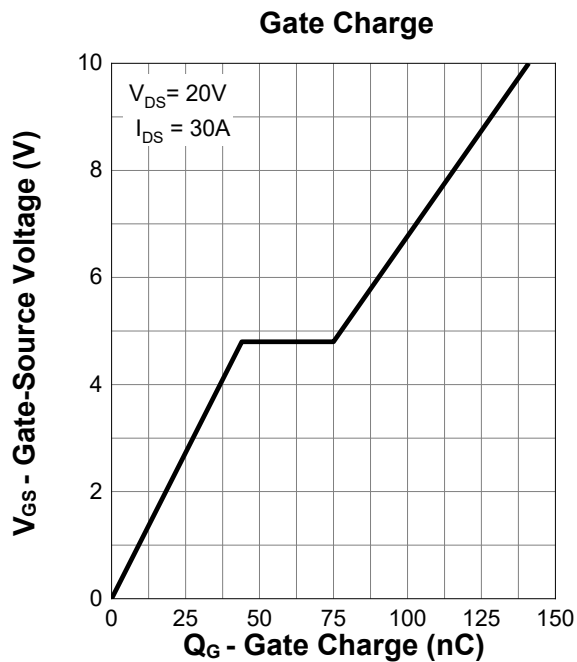
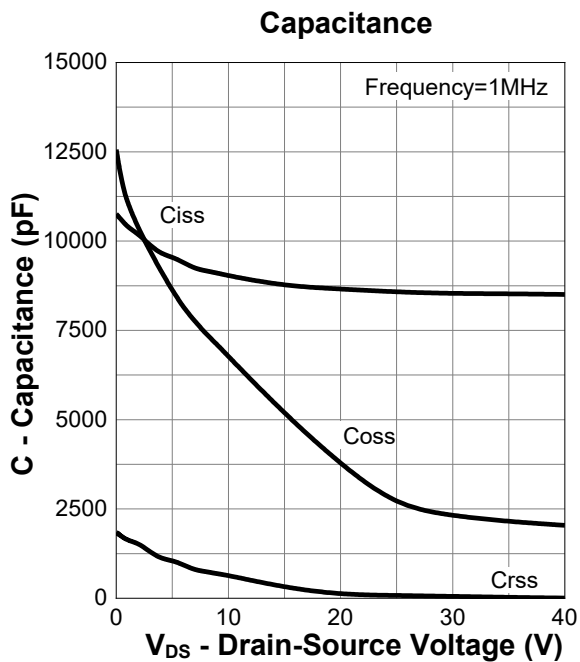
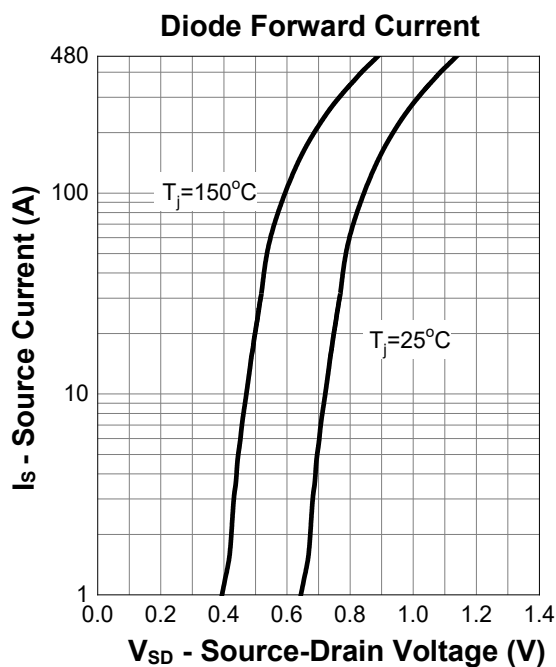
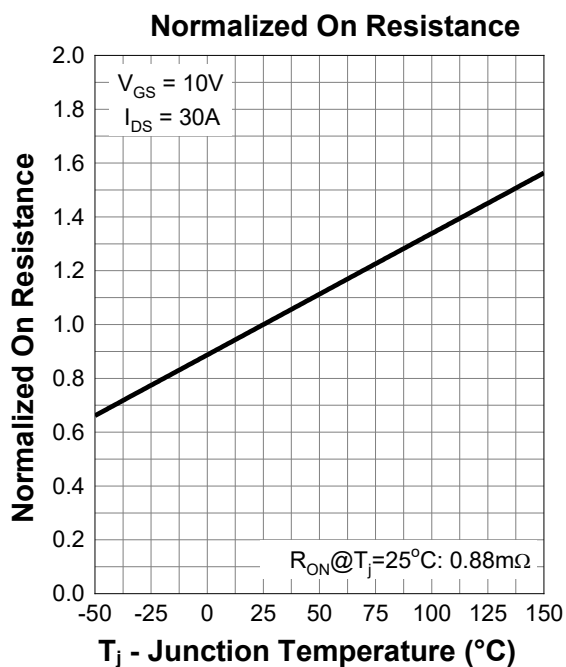
7. Typical Characteristics



7. Typical Characteristics (cont.)

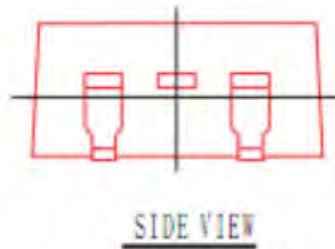
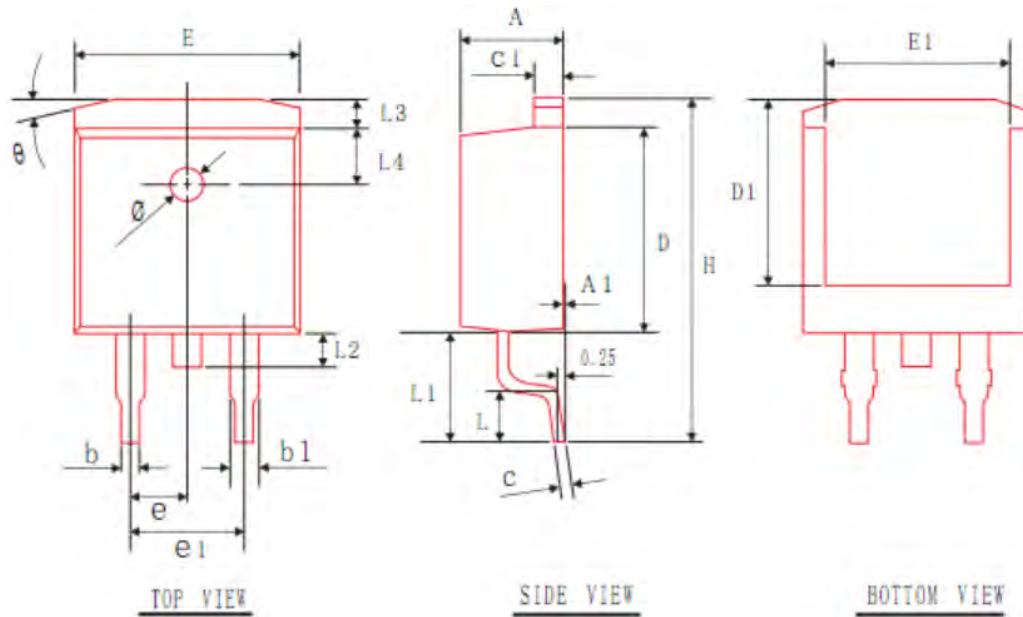


7. Typical Characteristics (cont.)



8.Package Dimensions

TO263



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	4.30	4.70
A1	0.00	0.25
b	0.70	0.90
b1	1.20	1.40
c	0.40	0.55
c1	1.25	1.35
D	9.00	9.20
D1	8.00	8.20
H	14.90	15.20
E	9.80	10.20
E1	7.85	8.15
e1	4.93	5.23
L	2.00	2.45
L1	4.60	5.00
L2	1.30	1.70
L3	1.15	1.35
L4	2.40	2.60
$\varnothing$	1.50 REF	
e	2.54 BSC	
θ	13° TYP	